

U.S.S.N. 10,761,477

Specification Amendments

Please replace paragraph 0046 with the following re-written paragraph:

[0046] During the anode phase, the wafer 48 has a positive charge and metal is etched from the seed layer 66 by electrolysis. Typically, about 20 angstroms of metal is removed from the seed layer 64 during the anode phase. The ratio of the quantity of metal electrolytically removed from the seed layer 66 during the anode phase to the quantity of metal electroplated onto the seed layer 66 during the cathode phase ~~to the quantity of metal electrolytically removed from the seed layer 66 during the anode phase~~ is typically about 2~5. This is accomplished by applying the pulsing electrical current to the wafer 48 for typically about 0.5 minutes.